RSC Advances



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CORRECTION



Cite this: RSC Adv., 2017, 7, 4645

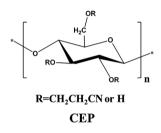
Correction: Raw product of rare-earth ore works as a high-k gate insulator for low-voltage operable organic field-effect transistors

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DOI: 10.1039/c7ra90001e www.rsc.org/advances

Correction for 'Raw product of rare-earth ore works as a high-*k* gate insulator for low-voltage operable organic field-effect transistors' by Xue-feng She *et al.*, *RSC Adv.*, 2016, **6**, 114593–114598.

The structure of the cyanoethylated pullulan polymer depicted in Fig. 1 was incorrect and the correct structure of the polymer unit is represented below:



The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.

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